bonding said silicon wafer to said glass wafer such that at least part of said silicon wafer first surface bonds to said glass wafer and at least part of said silicon wafer first surface overhangs said recess; and

after said bonding step, selectively removing a portion of said silicon wafer from said silicon wafer second surface through to said silicon wafer first surface such that a silicon structure is formed overhanging said recess.

14. (Amended) A method for making a thin structure, comprising:

providing a first wafer or substrate;

providing a second wafer having a first substantially planar surface and a second substantially planar surface;

forming a recess in said first wafer substrate;

bonding said second wafer to said first wafer such that at least part of said second wafer first surface bonds to said first wafer so that at least part of said second wafer first surface overhangs said recess; and

after said bonding step, selectively removing a portion of said second wafer from said second wafer second surface through to said second wafer first surface such that a thin structure is formed overhanging said recess.

19. (Amended) A method for making a thin structure as in claim 14, further comprising:

providing a patterned metal layer on the first substantially planar surface of the second wafer, such that the metal layer is patterned to coincide with said recess;

stopping the selective removal step at or near said metal layer to form the thin structure; and

removing said metal layer.

20. (Newly Presented) A method for making a thin structure comprising the steps of:

providing a first substrate having a first substantially planar surface and a second substantially planar surface;

providing a second substrate having a first substantially planar surface and a second substantially planar surface;

forming a recess in said first substantially planar surface of said first substrate and/or said first substantially planar surface of said second substrate;

securing said first substrate to said second substrate such that said first substantially planar surface of said first substrate faces said first substantially planar surface of said second substrate; and

after said securing step, selectively removing a portion of said first substrate from said second substantially planar surface of said first substrate such that a silicon structure is formed overhanging said recess.

21. (Newly Presented) A method for making a thin structure comprising the steps of:

providing a first substrate having a first substantially planar surface and a second substantially planar surface;

providing a second substrate having a first substantially planar surface and a second substantially planar surface;

forming a recess in said first substantially planar surface of said first substrate and/or said first substantially planar surface of said second substrate;

securing said first substrate to said second substrate such that said first substantially planar surface of said first substrate faces said first substantially planar surface of said second substrate; and

selectively removing a portion of said first substrate from said second substantially planar surface of said first substrate such that a thin structure is formed overhanging said recess, said thin structure being doped at a concentration of between zero and $1x10^{18}$ atm/cm^3.

22. (Newly Presented) A thin structure comprising:

a first substrate having a first substantially planar surface and a second substantially planar surface;

a second substrate having a first substantially planar surface and a second substantially planar surface;

said first substrate being secured relative to said second substrate such that said first substantially planar surface of said first substrate faces said first substantially planar surface of said second substrate; and

a cavity defined by said first substantially planar surface of said first substrate and said first substantially planar surface of said second substrate, at least part of the first substrate having one or more openings extending from the second substantially planar surface of said first substrate to the first substantially planar surface of said first substrate and into said cavity, the one or more openings defining a thin structure that overhangs said cavity, said thin structure being doped at a concentration of between zero and $1x10^{18}$ atm/cm^3.

22. (Newly Presented) A method for making a thin structure, comprising:

providing a first substrate having a first substantially planar surface and a second substantially planar surface;

providing a second substrate having a first substantially planar surface and a second substantially planar surface;

forming a recess in said first substantially planar surface of said first substrate and/or said first substantially planar surface of said second substrate;

providing a metal layer on the first substantially planar surface of the second substrate adjacent said recess;

securing said second substrate to said first substrate such that said first substantially planar surface of said first substrate faces said first substantially planar surface of said second substrate;

selectively removing a portion of said second substrate from said second substrate second substantially planar surface through to said second substrate first substantially planar surface such that a thin structure is formed overhanging said recess;

stopping the selective removal step at or near said metal layer to form the thin structure; and

removing said metal layer.